

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	21388	trench near2 isolation or STI	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:52
2	BRS	12	(trench near2 isolation or STI) with insulating with first and (trench near2 isolation or STI) with insulating with second and (trench near2 isolation or STI) with (liner or lining) with (etching or etched)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:54
3	BRS	9	(trench near2 isolation or STI) with insulating with first and (trench near2 isolation or STI) with insulating with second and (trench near2 isolation or STI) with conformal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:23
4	BRS	375	(trench near2 isolation or STI) with insulating with first and (trench near2 isolation or STI) with insulating with second	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:46
5	BRS	0	ex.perkissn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:42
6	BRS	0	"Pamela E Perkins"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:43
7	BRS	28	(trench near2 isolation or STI) with insulating near2 first and (trench near2 isolation or STI) near2 insulating with second	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:52
8	BRS	3	(trench near2 isolation or STI) with insulating near2 lower and (trench near2 isolation or STI) near2 insulating with upper	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:52
9	BRS	15	(trench near2 isolation or STI) same conformal adj (liner or lining)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:53
10	BRS	9	(trench near2 isolation or STI) with insulating with first and (trench near2 isolation or STI) with insulating with second and (trench near2 isolation or STI) with conformal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:56
11	BRS	228	(trench near2 isolation or STI) and insulating near2 first and insulating near2 second and conformal	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:04

	Type	Hits	Search Text	DBs	Time Stamp
12	BRS	150	(trench near2 isolation or STI) and insulating near2 first and insulating near2 second and (conformal same (etching or etched))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:57
13	BRS	96	(trench near2 isolation or STI) and insulating near2 first and insulating near2 second and (conformal with (etching or etched))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:58
14	BRS	83	(trench near2 isolation or STI) and insulating near2 first same insulating near2 second and (conformal with (etching or etched))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 17:58
15	BRS	67	(trench near2 isolation or STI) and insulating near2 first with insulating near2 second and (conformal with (etching or etched))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:00
16	BRS	13	(trench near2 isolation or STI) and insulating near2 first with trench and insulating near2 first with insulating near2 second and (conformal with (etching or etched))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:03
17	BRS	22	(trench near2 isolation or STI) and insulating near2 first with insulating near2 second and (conformal near3 (etching or etched))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:03
18	BRS	1349	(trench near2 isolation or STI) and insulating near2 first and insulating near2 second and (silicon adj nitride)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:05
19	BRS	22	(trench near2 isolation or STI) and insulating near2 first and insulating near2 second and (silicon adj nitride) with (lining or liner) with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:07
20	BRS	20	(trench near2 isolation or STI) and insulating near2 first same trench and insulating near2 second and (silicon adj nitride) with (lining or liner) with trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:08

	Type	Hits	Search Text	DBs	Time Stamp
21	BRS	669	(trench near2 isolation or STI) and insulating near2 first same trench and insulating near2 second same insulating near2 first	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:08
22	BRS	337	(trench near2 isolation or STI) and insulating near2 first same trench and insulating near2 second same insulating near2 first and silicon adj nitride same trench	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:08
23	BRS	40	(trench near2 isolation or STI) and insulating near2 first same trench and insulating near2 second same insulating near2 first and silicon adj nitride same trench same (lining or liner)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:17
24	BRS	81	(trench near2 isolation or STI) and insulating near2 first same trench and insulating near2 second same insulating near2 first and trench with (lining or liner)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:30
25	BRS	515	(trench near2 isolation or STI) and insulating with trench and trench with silicon adj nitride and trench with silicon adj oxide	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:31
26	BRS	33	(trench near2 isolation or STI) and insulating with trench and trench with silicon adj nitride with (lining or liner) and trench with silicon adj oxide with (lining or liner)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:36
27	BRS	48	(trench near2 isolation or STI) and insulating with trench and floating adj gate and hard adj mask	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:39
28	BRS	1	(trench near2 isolation or STI) and insulating with trench and first near2 floating adj gate and hard adj mask and second near2 floating adj gate and control adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:40
29	BRS	15	(trench near2 isolation or STI) and first near2 floating adj gate and hard adj mask and second near2 floating adj gate and control adj gate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 18:40

	Type	Hits	Search Text	DBs	Time Stamp
30	BRS	2	6265302.pn.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:00
31	BRS	810	438/404.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:01
32	BRS	1266	438/424.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:01
33	BRS	224	438/425.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:01
34	BRS	185	438/426.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:01
35	BRS	1680	438/427.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:02
36	BRS	803	438/700.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:03
37	BRS	313	438/437.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:05
38	BRS	281	438/594.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:06
39	BRS	261	438/221.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/08/08 19:06

Inventor Name Search Result

Your Search was:

Last Name = YUN
First Name = JAE-SUN

Application#	Patent#	Status	Date Filed	Title	Inventor Name 5
<u>60092553</u>	Not Issued	159	07/13/1998	METHOD FOR FABRICATING CELL OUT OF FLASH MEMORY DEVICE	YUN , JAE-SUN
<u>10629280</u>	Not Issued	041	07/29/2003	GATE STRUCTURES IN NONVOLATILE MEMORY DEVICES HAVING CURVED SIDE WALLS FORMED USING OXYGEN PATHWAYS AND METHODS OF FORMING SAME	YUN, JAE-SUN
<u>10601937</u>	Not Issued	030	06/24/2003	METHODS OF FORMING TRENCH ISOLATED INTEGRATED CIRCUIT DEVICES INCLUDING GROOVES, AND TRENCH ISOLATED INTEGRATED CIRCUIT DEVICES SO FORMED	YUN, JAE-SUN
<u>10333390</u>	Not Issued	030	01/17/2003	RELAYING METHOD FOR PROTECTING A TRANSFORMER USING A DIFFERENCE OF CURRENT	YUN, JAE-SUNG
<u>09352448</u>	<u>6153469</u>	150	07/13/1999	METHOD OF FABRICATING CELL OF FLASH MEMORY DEVICE	YUN , JAE-SUN

Inventor Search Completed: No Records to Display.

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Day : Sunday

Date: 8/8/2004

Time: 18:59:34



Inventor Name Search Result

Your Search was:

Last Name = SHIN
First Name = JIN-HYUN

Application#	Patent#	Status	Date Filed	Title	Inventor Name 3
10629280	Not Issued	041	07/29/2003	GATE STRUCTURES IN NONVOLATILE MEMORY DEVICES HAVING CURVED SIDE WALLS FORMED USING OXYGEN PATHWAYS AND METHODS OF FORMING SAME	SHIN, JIN-HYUN
10601937	Not Issued	030	06/24/2003	METHODS OF FORMING TRENCH ISOLATED INTEGRATED CIRCUIT DEVICES INCLUDING GROOVES, AND TRENCH ISOLATED INTEGRATED CIRCUIT DEVICES SO FORMED	SHIN, JIN-HYUN
10447254	Not Issued	093	05/28/2003	FLASH MEMORY DEVICES HAVING A SLOPED TRENCH ISOLATION STRUCTURE AND METHODS OF FABRICATING THE SAME	SHIN, JIN-HYUN

Inventor Search Completed: No Records to Display.

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